

ABSTRACT

BONDING METHOD OF WAFER RETAINING RING

The present invention provides a bonding method of a wafer retaining ring, which method comprises the following steps. First, a substrate and a high molecular retaining ring are provided. The bonding face of the high molecular retaining ring is processed by flame or plasma to let its surface generate reaction. Next, bonding faces of the substrate and the high molecular retaining ring are sandblasted and then wiped clean by dissolvent. Finally, epoxy is used to join the substrate and the high molecular retaining ring together. The wafer retaining ring of the present invention will not fall off and has better retaining effect.

FIGURE 4